

CLAIMS

1. (original) A method for processing electrical signals, comprising:
applying an input signal to a source follower;
sensing drain current of the source follower;
multiplying the sensed drain current; and
applying the multiplied sensed drain current to an output of the source follower.
2. (original) The invention of claim 1, wherein a folded cascode device senses the drain current.
3. (original) The invention of claim 1, wherein a current mirror multiplies the sensed drain current.
4. (currently amended) The invention of claim 3, wherein:
the source follower and the current mirror are both implemented using a single first type of device; and
the drain current is sensed using a device of a second type different from the first type.
5. (currently amended) The invention of claim 4, wherein:
the source follower and the current mirror are both implemented using NMOS devices;
the device used to sense the drain current is implemented using a PMOS device.
6. (original) A circuit comprising:
a source follower;
a first device connected to sense drain current of the source follower; and
a current mirror connected to multiply the sensed drain current for application to an output of the source follower.
7. (original) The invention of claim 6, wherein the first device is a folded cascode device.
8. (currently amended) The invention of claim 6, wherein:
the source follower and the current mirror are both implemented using a single first type of device; and
the first device is of a second type different from the first type.
9. (currently amended) The invention of claim 8, wherein:
the source follower and the current mirror are both implemented using NMOS devices; and
the first device is implemented using a PMOS device.
10. (original) The invention of claim 6, wherein the circuit is an integrated circuit.
11. (original) A circuit comprising:
a transistor M3;
a transistor M2 connected at a first channel node to a second channel node of the transistor M3,
wherein:
a gate node of the transistor M2 is connected to an input VIN; and
a second channel node of the transistor M2 is connected to an output VOUT;
a transistor M0 connected at a first channel node to the output VOUT;

8 a transistor M4 connected at a first channel node to the second channel node of the transistor M3;
9 and
10 a transistor M1 connected at a first channel node and a gate node to a second channel node of the
11 transistor M4 and to a gate node of the transistor M0, wherein a second channel node of the transistor M1
12 is connected to a second channel node of the transistor M0.

1 12. (original) The invention of claim 11, wherein, when (1) a first channel node of the
2 transistor M3 is connected to a first supply voltage, (2) the second channel nodes of the transistors M0
3 and M1 are connected to a second supply voltage, (3) a gate node of the transistor M3 is connected to a
4 first gate bias voltage, and (4) a gate node of the transistor M4 is connected to a second gate bias voltage,
5 an output voltage appearing at the output VOUT is proportional to an input voltage applied at the input
6 VIN.

1 13. (canceled)

1 14. (original) The invention of claim 12, wherein:
2 the transistor M3 functions as a current source for the circuit;
3 the transistors M0 and M2 function as a source follower;
4 the transistors M0 and M1 function as a current mirror;
5 the transistor M4 senses a drain current at the transistor M2; and
6 the current mirror multiplies the sensed drain current and applies the multiplied sensed drain
7 current to the output VOUT.

1 15. (original) The invention of claim 11, wherein:
2 the transistors M0, M1, and M2 are of a first type; and
3 the transistors M3 and M4 are of a second type different from the first type.

1 16. (original) The invention of claim 15, wherein the first type is NMOS transistors and the
2 second type is PMOS transistors.

1 17. (currently amended) The invention of claim 14, wherein:
2 the source follower and the current mirror are both implemented using a single first type of
3 device; and
4 the transistor M4 is of a second type different from the first type.

1 18. (currently amended) The invention of claim 17, wherein:
2 the source follower and the current mirror are both implemented using NMOS devices; and
3 the transistor M4 is a PMOS device.

1 19. (original) The invention of claim 11, wherein the circuit is an integrated circuit.

1 20. (new) The invention of claim 1, further comprising applying a current generated by a
2 current source to both the source follower and a device used to sense the drain current of the source
3 follower.

1 21. (new) The invention of claim 6, further comprising a current source connected to apply
2 a current to both the source follower and the first device.